

## Silicon Carbide Schottky Barrier Diode

$V_{RRM}$	650 V	$I_F$	4 A
$V_{F(Typ.)}$	1.5 V	$Q_C$	6.4 nC

### Features

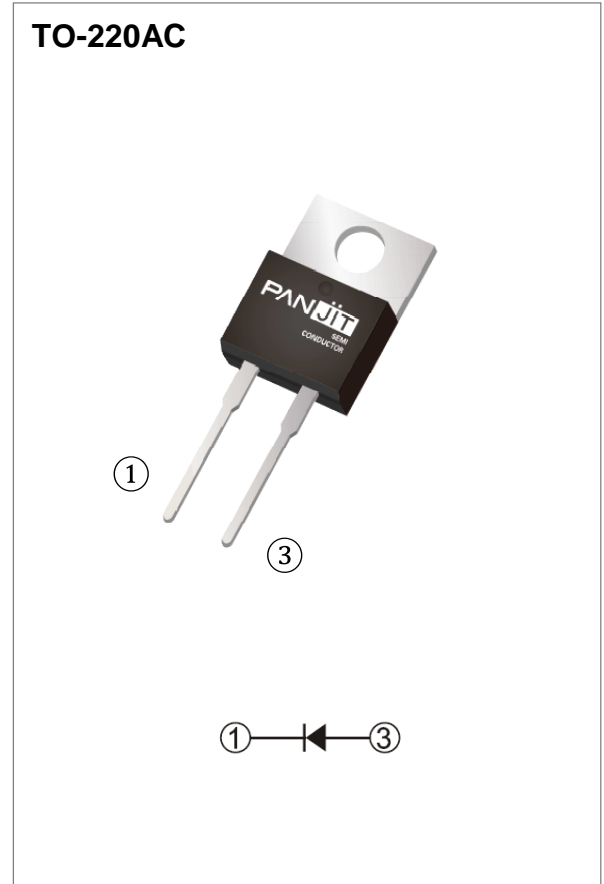
- Temperature Independent Switching Behavior
- High Surge Current Capability
- Positive Temperature Coefficient on  $V_F$
- Low Conduction Loss
- Zero Reverse Recovery
- High junction temperature 175 °C
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case: TO-220AC molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.067 ounces, 1.89 grams

### Application

- PFC, UPS, PV Inverter, EV Charging Station, Welder



### Maximum Ratings and Thermal Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	LIMIT	UNITS
Repetitive Peak Reverse Voltage		$V_{RRM}$	650	V
DC Blocking Voltage		$V_{DC}$	650	V
Continuous Forward Current	$T_C = 155\text{ }^\circ\text{C}$	$I_F$	4	A
Repetitive Peak Surge Current <i>Half Sine Wave, D=0.1</i>	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$	$I_{FRM}$	20	A
	$T_C = 125\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$		16	
Peak Forward Surge Current <i>Half Sine Wave</i>	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$	$I_{FSM}$	20	A
	$T_C = 125\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$		16	
Peak Forward Surge Current $t_p = 10\text{us}$ , Pulse			280	
Maximum Power Dissipation		$P_{total}$	56	W
Operating Junction Temperature Range		$T_J$	-55~175	$^\circ\text{C}$
Storage Temperature Range		$T_{STG}$	-55~175	$^\circ\text{C}$

**Electrical Characteristics** ( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Forward Voltage Drop	$V_F$	$I_F = 4\text{ A}, T_J = 25\text{ }^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 4\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	1.8	-	
Reverse Leakage Current	$I_R$	$V_R = 650\text{ V}, T_J = 25\text{ }^\circ\text{C}$	-	2	40	$\mu\text{A}$
		$V_R = 650\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	0.02	-	mA
Total Capacitive Charge	$Q_C$	$I_F = 4\text{ A}, V_R = 400\text{V}$	-	6.4	-	nC
Total Capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$	-	146	-	pF
		$V_R = 200\text{V}, f = 1\text{MHz}$	-	9.9	-	pF
		$V_R = 400\text{V}, f = 1\text{MHz}$	-	6.2	-	pF
Capacitance Stored Energy	$E_C$	$V_R = 400\text{V}$	-	0.8	-	$\mu\text{J}$
Thermal Resistance	$R_{\theta JC}$		-	2.68	-	$^\circ\text{C/W}$

TYPICAL CHARACTERISTIC CURVES

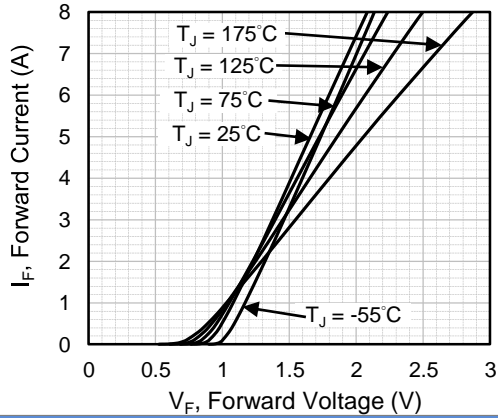


Fig.1 Forward Characteristics

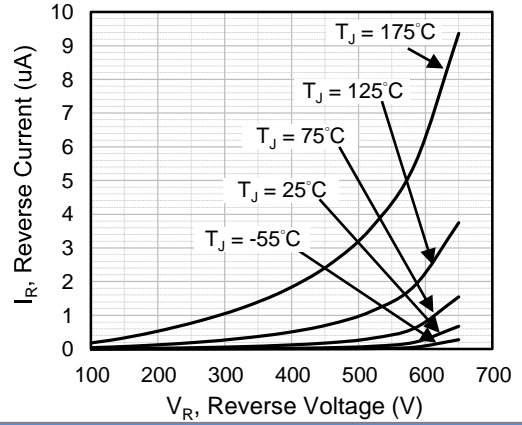


Fig.2 Reverse Characteristics

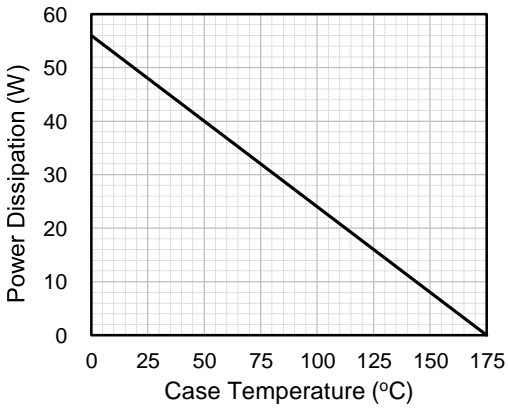


Fig.3 Power Derating Curve

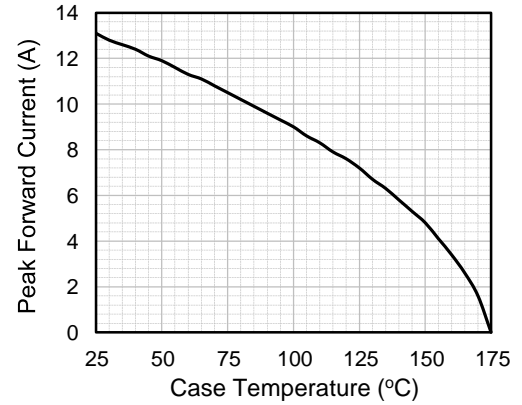


Fig.4 Current Derating Curve

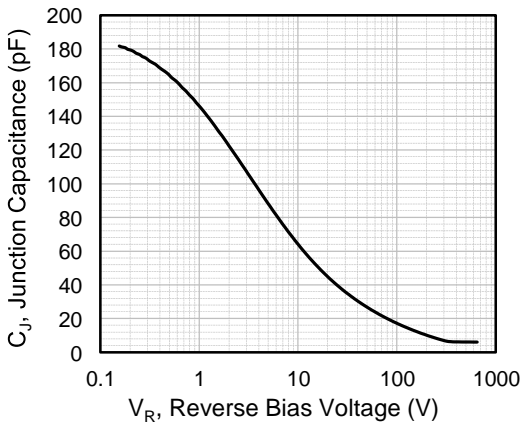


Fig.5 Typical Junction Capacitance

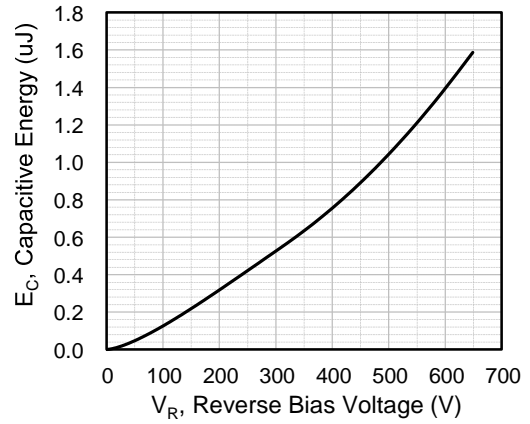


Fig.6 Capacitance Stored Energy

**Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PCDP0465G1	TO-220AC	50pcs / Tube	CDP0465G1

**Packaging Information**

